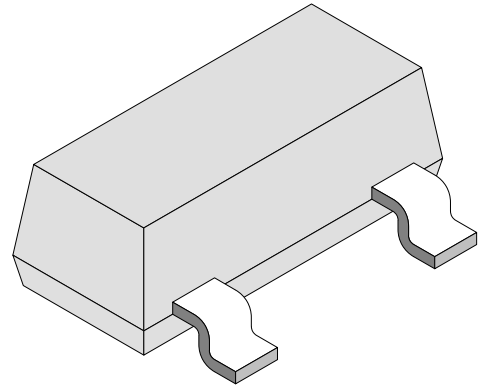


Silicon Epitaxial Planar Diode

Features

- Ultra fast switching speed
- Surface mount package ideally suited for automatic insertion
- High conductance



94 8550

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Non repetitive peak reverse voltage		V_{RM}	100	V
Repetitive peak reverse voltage =Working peak reverse voltage =DC Blocking voltage		V_{RRM} $=V_{RWM}$ $=V_R$	75	V
Peak forward surge current	$t_p=1\text{s}$	I_{FSM}	1	A
	$t_p=1\mu\text{s}$	I_{FSM}	2	A
Average forward current	half wave rectification with resistive load and $f \geq 50\text{ MHz}$, on ceramic substrate $8\text{mm} \times 10\text{mm} \times 0.7\text{mm}$	I_{FAV}	150	mA
Forward current	on ceramic substrate $8\text{mm} \times 10\text{mm} \times 0.7\text{mm}$	I_F	300	mA
Power dissipation	on ceramic substrate $8\text{mm} \times 10\text{mm} \times 0.7\text{mm}$	P_{tot}	350	mW
Junction and storage temperature range		$T_j=T_{stg}$	-55...+150	$^\circ\text{C}$

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on ceramic substrate $8\text{mm} \times 10\text{mm} \times 0.7\text{mm}$	R_{thJA}	357	K/W

Electrical Characteristics

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	V_F			715	mV
	$I_F=10\text{mA}$	V_F			855	mV
	$I_F=50\text{mA}$	V_F			1	V
	$I_F=150\text{mA}$	V_F			1.25	V
Reverse current	$V_R=75\text{V}$	I_R			1	μA
	$V_R=75\text{V}, T_j=150^\circ\text{C}$	I_R			50	μA
	$V_R=25\text{V}, T_j=150^\circ\text{C}$	I_R			30	μA
Diode capacitance	$V_R=0, f=1\text{MHz}$	C_D			4	pF
Reverse recovery time	$I_F=10\text{mA}$ to $I_R=1\text{mA}, V_R=6\text{V}, R_L=100\Omega$	t_{rr}			6	ns

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

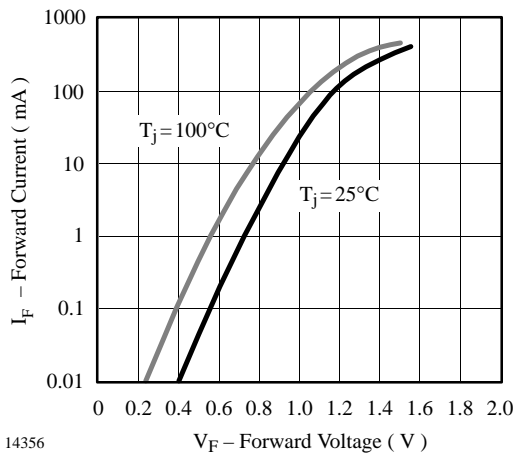


Figure 1. Forward Current vs. Forward Voltage

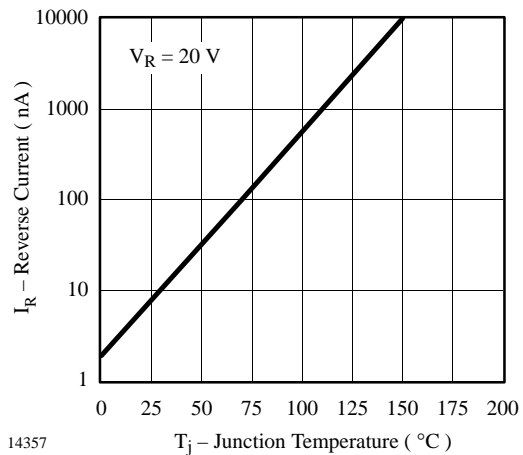
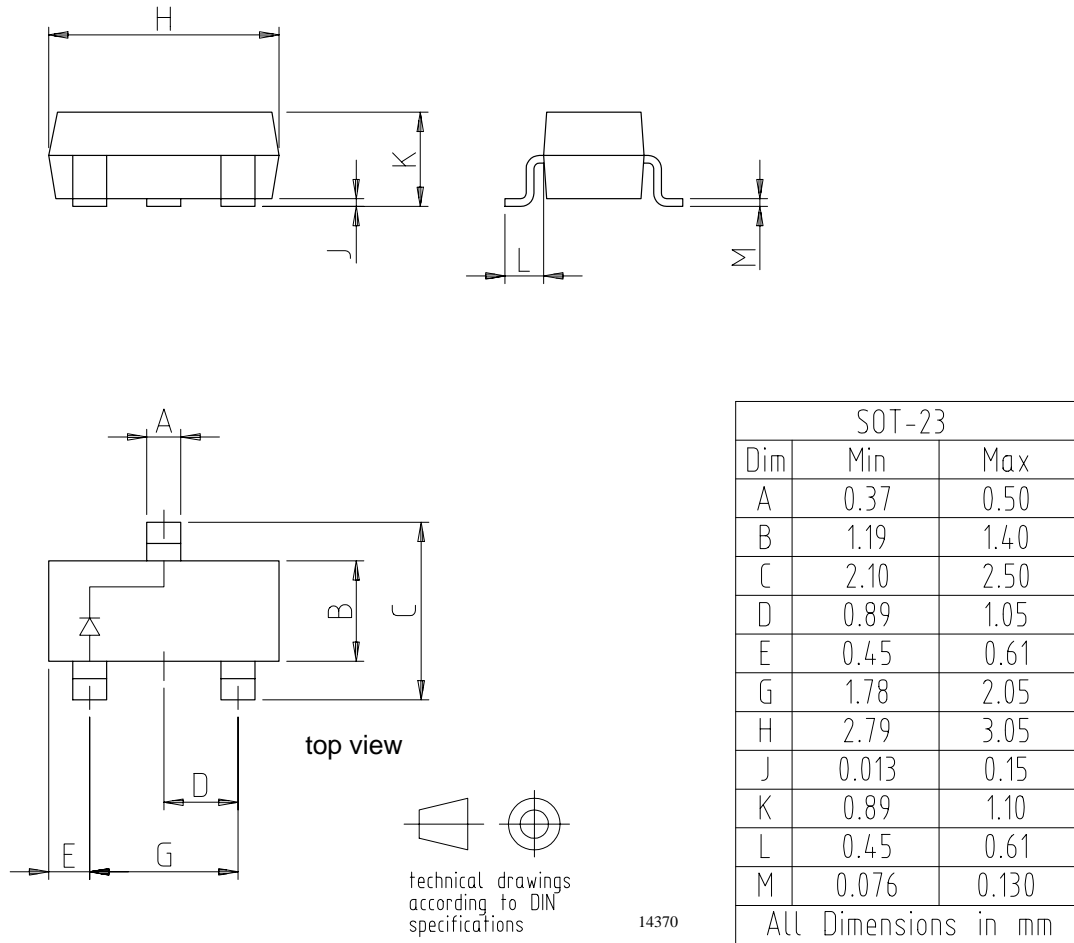


Figure 2. Reverse Current vs. Junction Temperature

Dimensions in mm



Case: SOT23, plastic
 Terminals: Solderable per MIL-STD-202, Method 208
 Polarity: cathode band
 Marking: KA6
 Approx. weight: SOT23 0.008 grams

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems
with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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